



Pressure contact
Low switching losses
High power cycling capability
Distributed amplified gate for high di_T/dt

Fast Stud Thyristor Type TF261-160-14

Mean on-state current				I _{TAV}		160 A	
Repetitive peak off-state voltage				V _{DRM}		800...1400 V	
Repetitive peak reverse voltage				V _{RRM}			
Turn-off time				t _q		20.0, 25.0, 32.0, 40.0 μs	
V _{DRM} , V _{RRM} , V	800	900	1000	1100	1200	1300	1400
Voltage code	8	9	10	11	12	13	14
T _{ij} , °C	−60...+125						

MAXIMUM ALLOWABLE RATINGS

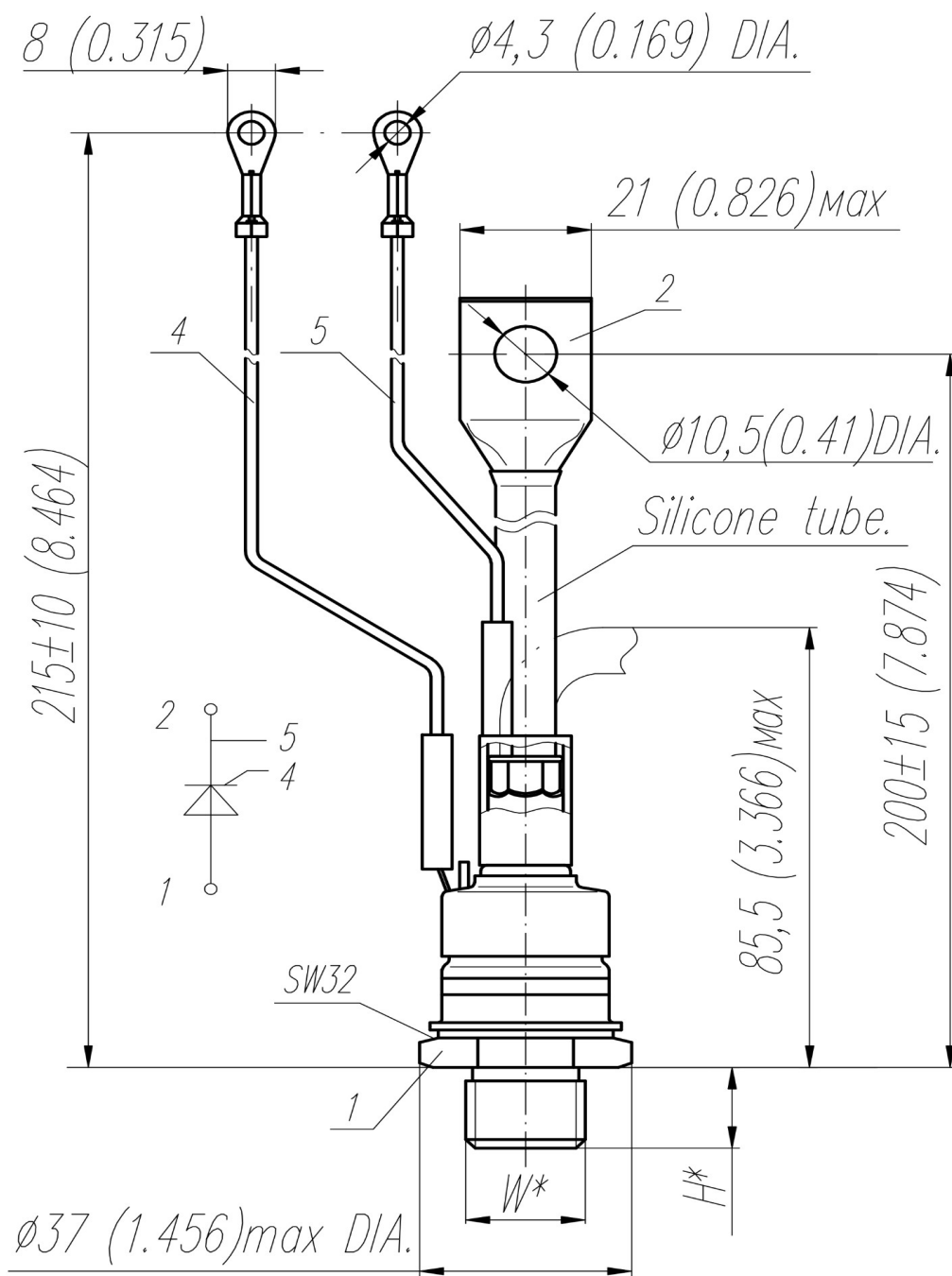
Symbols and parameters		Units	Values	Test conditions	
ON-STATE					
I_{TAV}	Maximum allowable mean on-state current	A	156 160 233	$T_c=85\text{ }^{\circ}\text{C}$; $T_c=83\text{ }^{\circ}\text{C}$; $T_c=55\text{ }^{\circ}\text{C}$; 180° half-sine wave; 50 Hz	
I_{TRMS}	RMS on-state current	A	251	$T_c=83\text{ }^{\circ}\text{C}$; 180° half-sine wave; 50 Hz	
I_{TSM}	Surge on-state current	kA	5.5 6.5	$T_j=T_{j\text{ max}}$ $T_j=25\text{ }^{\circ}\text{C}$	180° half-sine wave; $t_p=10\text{ ms}$; single pulse; $V_D=V_R=0\text{ V}$; Gate pulse: $I_G=2\text{ A}$; $V_G=20\text{ V}$; $t_{GP}=50\text{ }\mu\text{s}$; $di_G/dt=1\text{ A}/\mu\text{s}$
			6.0 7.0	$T_j=T_{j\text{ max}}$ $T_j=25\text{ }^{\circ}\text{C}$	180° half-sine wave; $t_p=8.3\text{ ms}$; single pulse; $V_D=V_R=0\text{ V}$; Gate pulse: $I_G=2\text{ A}$; $V_G=20\text{ V}$; $t_{GP}=50\text{ }\mu\text{s}$; $di_G/dt=1\text{ A}/\mu\text{s}$
I^2t	Safety factor	$A^2s\cdot 10^3$	150 210	$T_j=T_{j\text{ max}}$ $T_j=25\text{ }^{\circ}\text{C}$	180° half-sine wave; $t_p=10\text{ ms}$; single pulse; $V_D=V_R=0\text{ V}$; Gate pulse: $I_G=2\text{ A}$; $V_G=20\text{ V}$; $t_{GP}=50\text{ }\mu\text{s}$; $di_G/dt=1\text{ A}/\mu\text{s}$
			140 200	$T_j=T_{j\text{ max}}$ $T_j=25\text{ }^{\circ}\text{C}$	180° half-sine wave; $t_p=8.3\text{ ms}$; single pulse; $V_D=V_R=0\text{ V}$; Gate pulse: $I_G=2\text{ A}$; $V_G=20\text{ V}$; $t_{GP}=50\text{ }\mu\text{s}$; $di_G/dt=1\text{ A}/\mu\text{s}$
BLOCKING					
V_{DRM}, V_{RRM}	Repetitive peak off-state and Repetitive peak reverse voltages	V	800...1400	$T_{j\text{ min}} < T_j < T_{j\text{ max}}$; 180° half-sine wave; 50 Hz; Gate open	
V_{DSM}, V_{RSM}	Non-repetitive peak off-state and Non-repetitive peak reverse voltages	V	900...1500	$T_{j\text{ min}} < T_j < T_{j\text{ max}}$; 180° half-sine wave; single pulse; Gate open	
V_D, V_R	Direct off-state and Direct reverse voltages	V	$0.6\cdot V_{DRM}$ $0.6\cdot V_{RRM}$	$T_j=T_{j\text{ max}}$; Gate open	

TRIGGERING				
I_{FGM}	Peak forward gate current	A	5	$T_j = T_{j\max}$
V_{RGM}	Peak reverse gate voltage	V	5	
P_G	Gate power dissipation	W	3	$T_j = T_{j\max}$ for DC gate current
SWITCHING				
$(di_T/dt)_{crit}$	Critical rate of rise of on-state current non-repetitive ($f=1$ Hz)	A/ μ s	1000	$T_j = T_{j\max}$; $V_D = 0.67 \cdot V_{DRM}$; $I_{TM} = 320$ A; Gate pulse: $I_G = 2$ A; $V_G = 20$ V; $t_{GP} = 50$ μ s; $di_G/dt = 2$ A/ μ s
THERMAL				
T_{stg}	Storage temperature	$^{\circ}$ C	-60...+50	
T_j	Operating junction temperature	$^{\circ}$ C	-60...+125	
MECHANICAL				
M	Tightening torque	Nm	20...30	
a	Acceleration	m/s ²	100	

CHARACTERISTICS

Symbols and parameters		Units	Values	Conditions	
ON-STATE					
V _{TM}	Peak on-state voltage, max	V	1.85	T _j =25 °C; I _{TM} =502 A	
V _{T(TO)}	On-state threshold voltage, max	V	1.123	T _j =T _{j max} ;	
r _T	On-state slope resistance, max	mΩ	1.524	0.5 π I _{TAV} < I _T < 1.5 π I _{TAV}	
I _H	Holding current, max	mA	250	T _j =25 °C; V _D =12 V; Gate open	
BLOCKING					
I _{DRM} , I _{RRM}	Repetitive peak off-state and Repetitive peak reverse currents, max	mA	50	T _j =T _{j max} ; V _D =V _{DRM} ; V _R =V _{RRM}	
(dv _D /dt) _{crit}	Critical rate of rise of off-state voltage ¹⁾ , min	V/μs	200, 320, 500, 1000, 1600, 2000, 2500	T _j =T _{j max} ; V _D =0.67·V _{DRM} ; Gate open	
TRIGGERING					
V _{GT}	Gate trigger direct voltage, max	V	3.00 2.50 1.50	T _j = T _{j min} T _j =25 °C T _j = T _{j max}	V _D =12 V; I _D =3 A; Direct gate current
I _{GT}	Gate trigger direct current, max	mA	400 250 150	T _j = T _{j min} T _j = 25 °C T _j = T _{j max}	
V _{GD}	Gate non-trigger direct voltage, min	V	0.70	T _j =T _{j max} ; V _D =0.67·V _{DRM} ;	
I _{GD}	Gate non-trigger direct current, min	mA	55.00	Direct gate current	
SWITCHING					
t _{gd}	Delay time, max	μs	0.70	T _j =25 °C; V _D =600 V; I _{TM} =I _{TAV} ;	
t _{gt}	Turn-on time ²⁾ , max	μs	1.60, 2.00, 2.50, 3.20	di/dt=200 A/μs; Gate pulse: I _G =2 A; V _G =20 V; t _{GP} =50 μs; di _G /dt=2 A/μs	
t _q	Turn-off time ³⁾ , max	μs	20.0, 25.0, 32.0, 40.0	dv _D /dt=50 V/μs; T _j =T _{j max} ; I _{TM} = I _{TAV} ; di _R /dt=-10 A/μs; V _R =100V; V _D =0.67 V _{DRM}	
THERMAL					
R _{thjc}	Thermal resistance, junction to case, max	°C/W	0.150	Direct current	
MECHANICAL					
m	Weight, maxc	g	280		
D _s	Surface creepage distance	mm (inch)	12.4 (4.882)		
D _a	Air strike distance	mm (inch)	12.4 (4.882)		

PART NUMBERING GUIDE								NOTES									
TF	261	160	14	A2	H3	K4	N	1) Critical rate of rise of off-state voltage									
1	2	3	4	5	6	7	8	Symbol of Group		P2	K2	E2	A2	T1	P1	M1	
								(dv _D /dt) _{crit} , V/μs		200	320	500	1000	1600	2000	2500	
1. Fast Thyristor								2)Turn-on time									
2. Design version								Symbol of group		T4		P4		M4		K4	
3. Mean on-state current, A								t _{gr} , μs		1.60		2.00		2.50		3.20	
4. Voltage code								3)Turn-off time (dv _D /dt=50 V/μs)									
5. Critical rate of rise of off-state voltage								Symbol of group		P3		M3		K3		H3	
6. Group of turn-off time (dv _D /dt=50 V/μs)								t _{qr} , μs		20.0		25.0		32.0		40.0	
7. Group of turn-on time																	
8. Ambient conditions: N – normal; T – tropica																	



Type of screw	W	H
Metric Screw Type A	M16x1,5 – 8g	13
Metric Screw Type B (upon request)	M20x1,5 – 8g	15

Polarity	Example of code designation	Reference designation	Colors		
			Anode	Cathode	Gate
Anode to stud	TF261-160-14		-	Red tube	White

All dimensions in millimeters (inches)